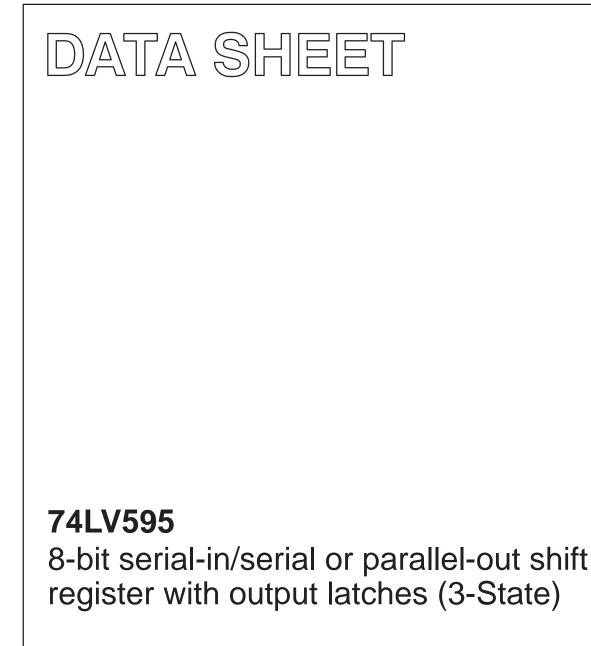
### INTEGRATED CIRCUITS



Product specification IC24 Data Handbook 1998 Apr 20



Philips Semiconductors

### 74LV595

#### FEATURES

- Optimized for Low Voltage applications: 1.0V to 3.6V
- Accepts TTL input levels between V<sub>CC</sub> = 2.7V and V<sub>CC</sub> = 3.6V
- Typical V<sub>OLP</sub> (output ground bounce) < 0.8V at V<sub>CC</sub> = 3.3V,  $T_{amb} = 25^{\circ}C$
- Typical V<sub>OHV</sub> (output V<sub>OH</sub> undershoot) > 2V at V<sub>CC</sub> = 3.3V,  $T_{amb} = 25^{\circ}C$
- 8-bit serial input
- 8-bit serial or parallel output
- Storage register with 3-State outputs
- Shift register with direct clear
- Output capability: parallel outputs; bus driver
- serial output; standard
- I<sub>CC</sub> category: MSI

#### APPLICATIONS

- Serial-to-parallel data conversion
- Remote control holding register

#### DESCRIPTION

The 74LV595 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC/HCT595.

The74LV595 is an 8-stage serial shift register with a storage register and 3-State outputs. The shift register and storage register have separate clocks.

Data is shifted on the positive-going transitions of the SH<sub>CP</sub> input. The data in each register is transferred to the storage register on a positive-going transition of the  $ST_{CP}$  input. If both clocks are connected together, the shift register will always be one clock pulse ahead of the storage register.

The shift register has a serial input (D<sub>S</sub>) and a serial standard output (Q7') all for cascading. It is also provided with asynchronous reset (active LOW) for all 8 shift register stages. The storage register has 8 parallel 3-State bus driver outputs. Data in the storage register appears at the output whenever the output enable input ( $\overline{OE}$ ) is LOW.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t <sub>PHL</sub> /t <sub>PLH</sub>	Propagation delay $SH_{CP}$ to $Q_{7'}$ $ST_{CP}$ to $Q_{7'}$ $MR$ to $Q_{7'}$	C <sub>L</sub> = 15pF V <sub>CC</sub> = 3.3V	15 16 14	ns
f <sub>max</sub>	Maximum clock frequency $SH_{CP}$ , $ST_{CP}$	1	77	MHz
CI	Input capacitance		3.5	pF
C <sub>PD</sub>	Power dissipation capacitance per gate	V <sub>CC</sub> = 3.3V Notes 1 and 2	115	pF

NOTES:

 $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W)  $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} + \sum (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$  $f_i$  = input frequency in MHz;  $C_L$  = output load capacitance in pF;  $f_o =$  output frequency in MHz;  $V_{CC} =$  supply voltage in V;  $\sum_{i=1}^{n} (C_{L} \times V_{CC}^{2} \times f_{o}) = \text{sum of the outputs.}$ 2. The condition is V<sub>1</sub> = GND to V<sub>CC</sub>.

#### **ORDERING AND PACKAGE INFORMATION**

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	PKG. DWG. #
16-Pin Plastic DIL	–40°C to +125°C	74LV595 N	74LV595 N	SOT38-4
16-Pin Plastic SO	-40°C to +125°C	74LV595 D	74LV595 D	SOT109-1
16-Pin Plastic SSOP Type II	–40°C to +125°C	74LV595 DB	74LV595 DB	SOT338-1
16-Pin Plastic TSSOP Type I	–40°C to +125°C	74LV595 PW	74LV595PW DH	SOT403-1

#### QUICK REFERENCE DATA GND = 0V; $T_{amb} = 25^{\circ}C$ ; $t_r = t_f \le 2.5 \text{ ns}$

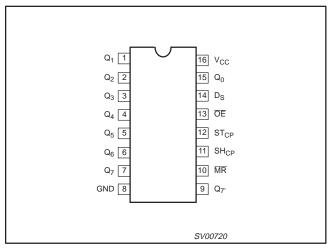
### Product specification

### 74LV595

#### **PIN DESCRIPTION**

PIN NUMBER	SYMBOL	FUNCTION
15, 1, 2, 3, 4, 5, 6, 7	$Q_0$ to $Q_7$	Parallel data output
8	GND	Ground (0V)
9	Q <sub>7'</sub>	Serial data output
10	MR Master reset (active LOW)	
11	SH <sub>CP</sub>	Shift register clock input
12	ST <sub>CP</sub>	Storage register clock input
13	ŌĒ	Output enable input (active LOW)
14	D <sub>S</sub>	Serial data input
16	V <sub>CC</sub>	Positive supply voltage

#### **PIN CONFIGURATION**



#### **FUNCTION TABLE**

	INPUTS				OUTF	PUTS	FUNCTION
SH <sub>CP</sub>	ST <sub>CP</sub>	ŌĒ	MR	D <sub>S</sub>	Q <sub>7'</sub> Qn		FUNCTION
Х	Х	L	L	Х	L	NC	A LOW level on $\overline{\text{MR}}$ only affects the shift registers
Х	î	L	L	Х	L	L	Empty shift register loaded into storage register
Х	Х	Н	L	Х	L	Z	Shift register clear. Parallel outputs in high-impedance OFF-states
Ŷ	х	L	Н	Н	Q <sub>6'</sub>	NC	Logic high level shifted into shift register stage 0. Contents of all shift register stages shifted through, e.g. previous state of stage 6 (internal $Q_{6'}$ ) appears on the serial output ( $Q_{7'}$ )
х	î	L	Н	х	NC	Q <sub>n'</sub>	Contents of shift register stages (internal Qn') are transferred to the storage register and parallel output stages
Ŷ	î	L	Н	х	Q <sub>6</sub> ,	Q <sub>n'</sub>	Contents of shift register shifted through. Previous contents of the shift register are transferred to the storage register and the parallel output stages

H = HIGH voltage level L = LOW voltage level X = Don't care

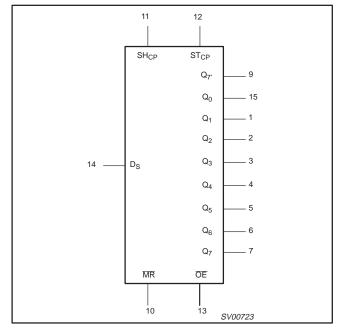
= High impedance OFF-state Ζ

NC = No change  $\uparrow = LOW-to-HIGH clock transition$ 

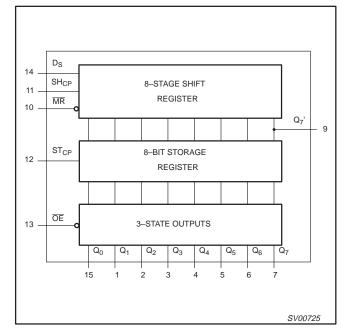
= HIGH-to-LOW transition

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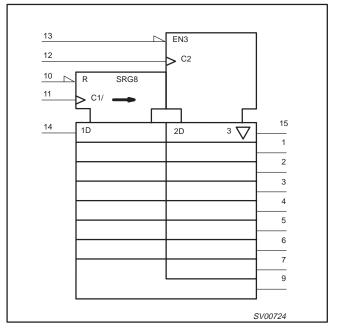
#### LOGIC SYMBOL



#### FUNCTIONAL DIAGRAM

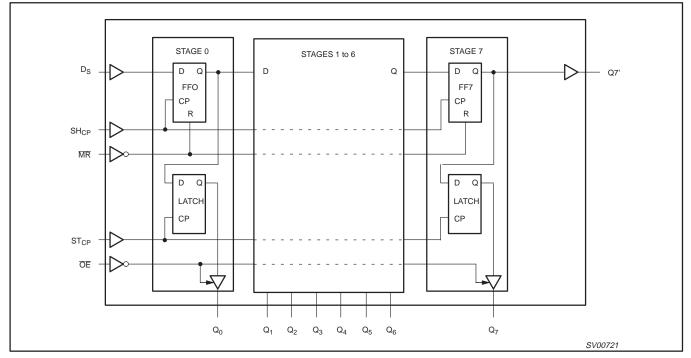


#### LOGIC SYMBOL (IEEE/IEC)

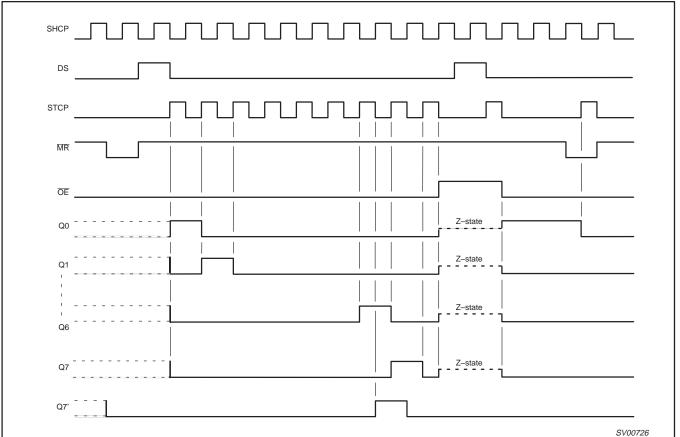


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#### LOGIC DIAGRAM



#### TIMING DIAGRAM



#### **RECOMMENDED OPERATING CONDITIONS**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CC</sub>	DC supply voltage	See Note1	1.0	3.3	3.6	V
VI	Input voltage		0	-	V <sub>CC</sub>	V
Vo	Output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	Operating ambient temperature range in free air	See DC and AC characteristics	-40 -40		+85 +125	°C
t <sub>r</sub> , t <sub>f</sub>	Input rise and fall times	$V_{CC} = 1.0V \text{ to } 2.0V$ $V_{CC} = 2.0V \text{ to } 2.7V$ $V_{CC} = 2.7V \text{ to } 3.6V$	- - -	- - -	500 200 100	ns/V

NOTE:

1. The LV is guaranteed to function down to  $V_{CC} = 1.0V$  (input levels GND or  $V_{CC}$ ); DC characteristics are guaranteed from  $V_{CC} = 1.2V$  to  $V_{CC} = 3.6V$ .

#### ABSOLUTE MAXIMUM RATINGS<sup>1, 2</sup>

In accordance with the Absolute Maximum Rating System (IEC 134) Voltages are referenced to GND (ground = 0V)

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V <sub>CC</sub>	DC supply voltage		–0.5 to +4.6	V
±Ι <sub>ΙΚ</sub>	DC input diode current	$V_{\rm I} < -0.5 \text{ or } V_{\rm I} > V_{\rm CC} + 0.5 V$	20	mA
±Іок	DC output diode current	$V_{\rm O}$ < -0.5 or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5V	50	mA
±IO	DC output source or sink current – standard outputs – bus driver outputs	$-0.5V < V_{O} < V_{CC} + 0.5V$	25 35	mA
±I <sub>GND</sub> , ±I <sub>CC</sub>	DC V <sub>CC</sub> or GND current for types with –standard outputs –bus driver outputs		50 70	mA
T <sub>stg</sub>	Storage temperature range		-65 to +150	°C
P <sub>TOT</sub>	Power dissipation per package –plastic DIL –plastic mini-pack (SO) –plastic shrink mini-pack (SSOP and TSSOP)	for temperature range: -40 to +125°C above +70°C derate linearly with 12mW/K above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	750 500 400	mW

NOTES:

 Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

#### **DC CHARACTERISTICS**

Over recommended operating conditions voltages are referenced to GND (ground = 0V)

					LIMITS			
SYMBOL	PARAMETER	TEST CONDITIONS	-4	0°C to +8	5°C	-40°C to +125°C		
			MIN	TYP <sup>1</sup>	MAX	MIN	MAX	1
		V <sub>CC</sub> = 1.2V	0.9			0.9		
VIH	HIGH level Input voltage	$V_{CC} = 2.0V$	1.4			1.4		V
	Vollago	V <sub>CC</sub> = 2.7 to 3.6V	2.0			2.0		1
		V <sub>CC</sub> = 1.2V			0.3		0.3	
VIL	LOW level Input voltage	$V_{CC} = 2.0V$			0.6		0.6	V
	Vollago	V <sub>CC</sub> = 2.7 to 3.6V			0.8		0.8	1
		$V_{CC}$ = 1.2V; $V_I = V_{IH}$ or $V_{IL;}$ – $I_O$ = 100 $\mu$ A		1.2				
V <sub>OH</sub>	HIGH level output	$V_{CC} = 2.0V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$	1.8	2.0		1.8		V
⊻он	voltage; all outputs	$V_{CC} = 2.7V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$	2.5	2.7		2.5		7 °
		$V_{CC}$ = 3.0V; $V_I$ = $V_{IH}$ or $V_{IL;}$ – $I_O$ = 100 $\mu$ A	2.8	3.0		2.8		1
V <sub>OH</sub>	HIGH level output voltage; STANDARD outputs	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 6mA$	2.40	2.82		2.20		v

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#### **DC CHARACTERISTICS (Continued)**

Over recommended operating conditions voltages are referenced to GND (ground = 0V)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					
STINDUL	PARAMETER	TEST CONDITIONS	-40°C to +85°C			-40°C to +125°C		
V <sub>OH</sub>	HIGH level output voltage; BUS driver outputs	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} -I_O = 8mA$	2.40	2.82		2.20		V
		$V_{CC}$ = 1.2V; $V_I$ = $V_{IH}$ or $V_{IL}$ ; $I_O$ = 100 $\mu$ A		0				
V <sub>OL</sub>	LOW level output	$V_{CC}$ = 2.0V; $V_I$ = $V_{IH}$ or $V_{IL}$ ; $I_O$ = 100 $\mu$ A		0	0.2		0.2	
VOL	voltage; all outputs	$V_{CC}$ = 2.7V; $V_I$ = $V_{IH}$ or $V_{IL}$ ; $I_O$ = 100 $\mu$ A		0	0.2		0.2	ľ
		$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 100 \mu A$		0	0.2		0.2	]
V <sub>OL</sub>	LOW level output voltage; STANDARD outputs	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} I_O = 6mA$		0.25	0.40		0.50	v
V <sub>OL</sub>	LOW level output voltage; BUS driver outputs	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} I_O = 8mA$		0.20	0.40		0.50	V
lı	Input leakage current	$V_{CC} = 3.6V; V_I = V_{CC} \text{ or } GND$			1.0		1.0	μA
I <sub>OZ</sub>	3-State output OFF-state current	$V_{CC} = 3.6V; V_I = V_{IH} \text{ or } V_{IL;}$ $V_O = V_{CC} \text{ or GND}$			5		10	μA
I <sub>CC</sub>	Quiescent supply current; MSI	$V_{CC} = 3.6V; V_I = V_{CC} \text{ or GND}; I_O = 0$			20.0		160	μΑ
$\Delta I_{CC}$	Additional quiescent supply current per input	$V_{CC} = 2.7V$ to 3.6V; $V_{I} = V_{CC} - 0.6V$			500		850	μA

NOTE:

1. All typical values are measured at  $T_{amb} = 25^{\circ}C$ .

#### **AC CHARACTERISTICS**

 $GND = 0V; t_r = t_f \le 2.5ns; C_L = 50pF; R_L = 1K\Omega$ 

SYMBOL	PARAMETER	WAVEFORM	CONDITION	_	LIMITS 40 to +85 °	C	LIMITS -40 to +125 °C		UNIT	
		Ι Γ	V <sub>CC</sub> (V)	MIN	TYP <sup>1</sup>	MAX	MIN	MAX		
		1.2	-	95	-	-	-			
t=	Propagation delay	Figure 1	2.0	- 1	32	61	- 1	75	ns	
t <sub>PHL</sub> /t <sub>PLH</sub>	SH <sub>CP</sub> to Q <sub>7</sub> '	rigure i	2.7	-	24	45	-	55	115	
			3.0 to 3.6	-	18 <sup>2</sup>	36	-	44		
		1.2	-	100	-	-	-			
tau tau	Propagation delay	Propagation delay	Figure 2	2.0		34	65	- 1	77	ns
TPHL/ <sup>t</sup> PLH ST <sub>CP</sub> to Q <sub>n</sub>	rigure 2	2.7	-	25	48	-	56	115		
	Ι Γ	3.0 to 3.6	-	19 <sup>2</sup>	38	-	45			
			1.2	-	85	-	-	-		
t	Propagation delay	Figure 5	2.0	-	29	56	-	66	ns	
t <sub>PHL</sub>	MR to Q7'		2.7	-	21	41	-	49	115	
			3.0 to 3.6	-	16 <sup>2</sup>	33	-	33		
			1.2	-	85	-	-	-		
tanutan	3-State output enable time	Figure 3	2.0	-	29	56	-	66	ns	
t <sub>PZH/</sub> t <sub>PZL</sub>	$\overline{OE}$ to $Q_n$		2.7	-	21	41	-	49	115	
		Ι Γ	3.0 to 3.6	-	16 <sup>2</sup>	33	-	39		
			1.2	-	65	-	-	-		
tt	t <sub>PHZ</sub> /t <sub>PLZ</sub> 3-State output disable time OE to Q <sub>n</sub>	Figure 3	2.0	-	24	40	-	49	ns	
'PHZ/'PLZ			2.7	-	18	32	-	37		
			3.0 to 3.6	-	14 <sup>2</sup>	26	-	30		

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#### AC CHARACTERISTICS (Continued)

GND = 0V;  $t_r = t_f \le 2.5$ ns;  $C_L = 50$ pF;  $R_L = 1K\Omega$ 

SYMBOL	PARAMETER	WAVEFORM	CONDITION	_	LIMITS 40 to +85 °	C		<b>IITS</b> <b>+125</b> ℃	UNIT			
			V <sub>CC</sub> (V)	MIN	TYP <sup>1</sup>	MAX	MIN	MAX				
			2.0	34	10	-	41	-				
t <sub>W</sub>	Shift clock pulse width HIGH or LOW	Figure 1	2.7	25	8	-	30	-	ns			
			3.0 to 3.6	20	6 <sup>2</sup>	-	24	-				
	<b>a</b>		2.0	34	7	-	41	-				
t <sub>W</sub>	Storage clock pulse width HIGH or LOW	Figure 2	2.7	25	5	-	30	-	ns			
			3.0 to 3.6	20	4 <sup>2</sup>	-	24	-				
			2.0	34	10	-	41	-				
t <sub>W</sub>	Master reset pulse width LOW	Figure 5	2.7	25	8	-	30	-	ns			
	width LOW		3.0 to 3.6	20	6 <sup>2</sup>	-	24	-	. – 1			
	t <sub>su</sub> Set-up time D <sub>S</sub> to SH <sub>CP</sub>					1.2	-	40	-	-	-	
+		Figure 4	2.0	26	14	-	31	-	ns			
usu		Figure 4	2.7	19	10	-	23	-				
			3.0 to 3.6	15	8 <sup>2</sup>	-	18	-				
			1.2	-	40	-	-	-				
+	Set-up time	Figure 2	2.0	26	14	-	31	-	ns			
t <sub>su</sub>	SH <sub>CP</sub> to ST <sub>CP</sub>	Figure 2	2.7	19	10	-	23	-	115			
			3.0 to 3.6	15	8 <sup>2</sup>	-	18	-				
			1.2	-	-10	-	-	-				
<b>t</b> .	Hold time	Figure 4	2.0	5	-4	-	5	-	ns			
t <sub>h</sub>	D <sub>S</sub> to SH <sub>CP</sub>	Figure 4	2.7	5	-3	-	5	-	115			
			3.0 to 3.6	5	-2 <sup>2</sup>	-	5	-				
		İ	1.2	-	-35	-	-	-				
+	Removal time	Figure 5	2.0	5	-12	-	5	-	ns			
rem	t <sub>rem</sub> MR to SH <sub>CP</sub>		2.7	5	-9	-	5	-	115			
			3.0 to 3.6	5	-7 <sup>2</sup>	-	5	-				
	Maximum clock		2.0	14	40	-	12	-				
f <sub>max</sub>	f <sub>max</sub> pulse frequency SH <sub>CP</sub> or ST <sub>CP</sub>	Figure 1, 2	2.7	19	58	-	16	-	MHz			
			3.0 to 3.6	24	70 <sup>2</sup>	-	20	-				

NOTES:

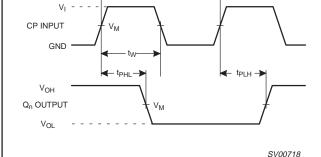
1. Unless otherwise stated, all typical values are at  $T_{amb}$  = 25°C.

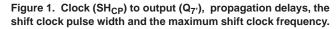
2. Typical value measured at V<sub>CC</sub> = 3.3V.

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#### AC WAVEFORMS

 $V_{M} = 1.5V \text{ at } V_{CC} \ge 2.7V$   $V_{M} = 0.5 * V_{CC} \text{ at } V_{CC} < 2.7V$   $V_{OL} \text{ and } V_{OH} \text{ are the typical output voltage drop that occur with the output load.}$   $V_{X} = V_{OL} + 0.3V \text{ at } V_{CC} \ge 2.7V$   $V_{X} = V_{OL} + 0.1V_{CC} \text{ at } V_{CC} < 2.7V$   $V_{Y} = V_{OH} - 0.3V \text{ at } V_{CC} \ge 2.7V$   $V_{Y} = V_{OH} - 0.1V_{CC} \text{ at } V_{CC} < 2.7V$ 





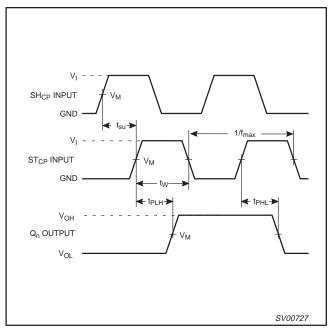


Figure 2. Storage clock  $(ST_{CP})$  to output  $(Q_n)$  propagation delays, the storage clock pulse width and the shift clock to storage clock set-up time.

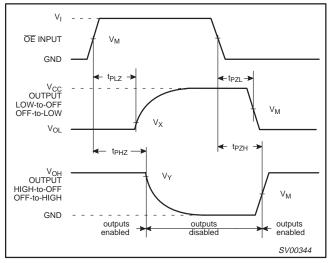


Figure 3. 3-State enable and disable times for input  $\overline{OE}$ .

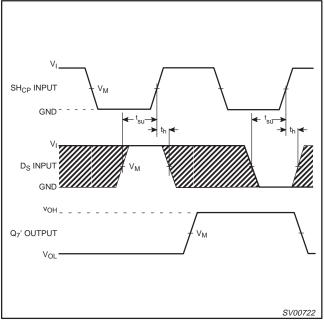


Figure 4. Data set-up and hold times for the data input (D<sub>S</sub>).

**AC WAVEFORMS (Continued)** 

### 74LV595

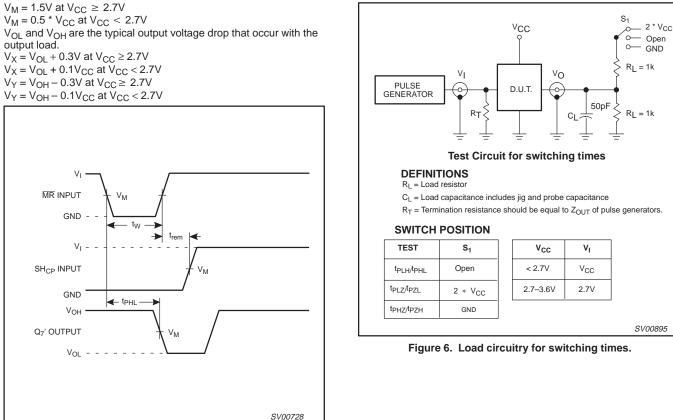
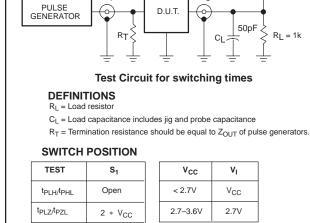
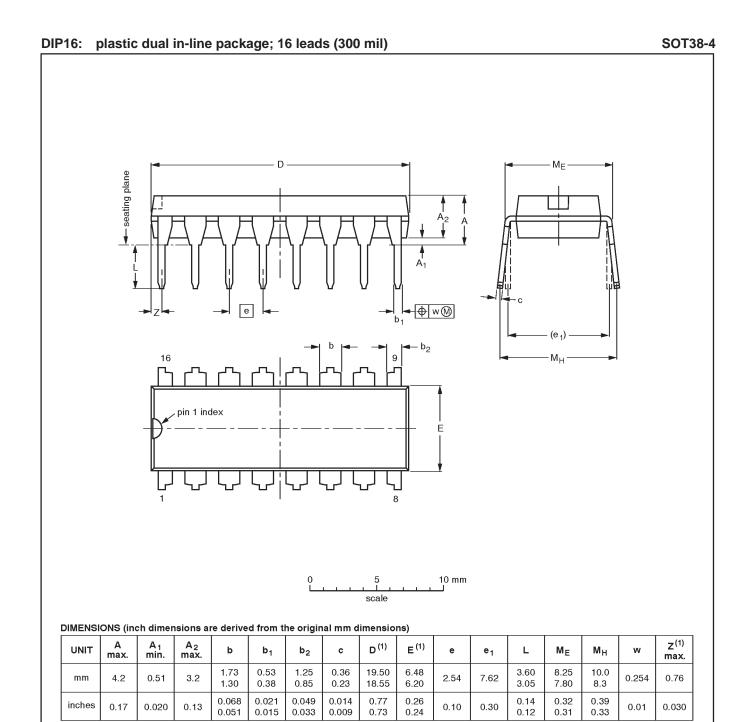


Figure 5. Master reset (MR) pulse width, the master reset to output (Q7') propagation delay and the master reset to shift clock (SH<sub>CP</sub>) removal time.

#### **TEST CIRCUIT**





#### Note

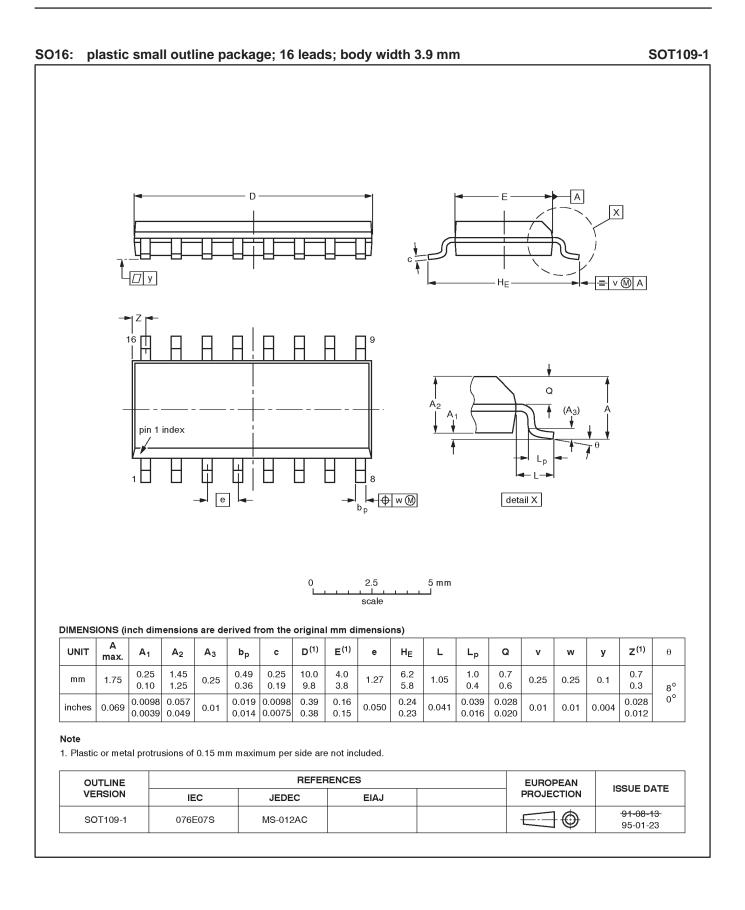
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFERENCES IEC JEDEC EIAJ				ISSUE DATE
VERSION	IEC					ISSUE DATE
SOT38-4						<del>-92-11-17</del> 95-01-14

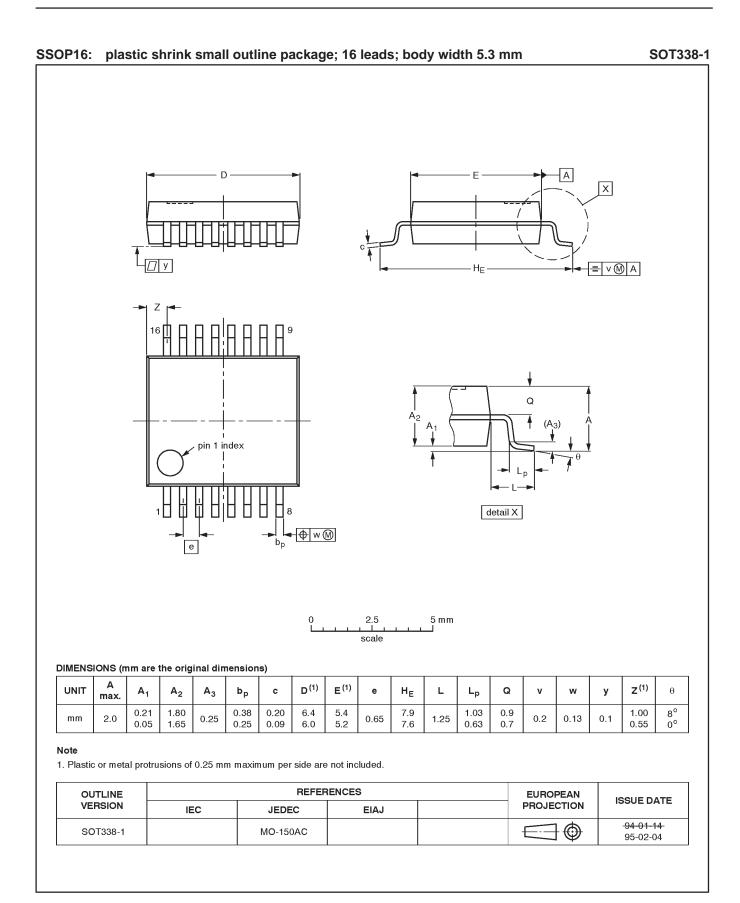
74LV595

Product specification

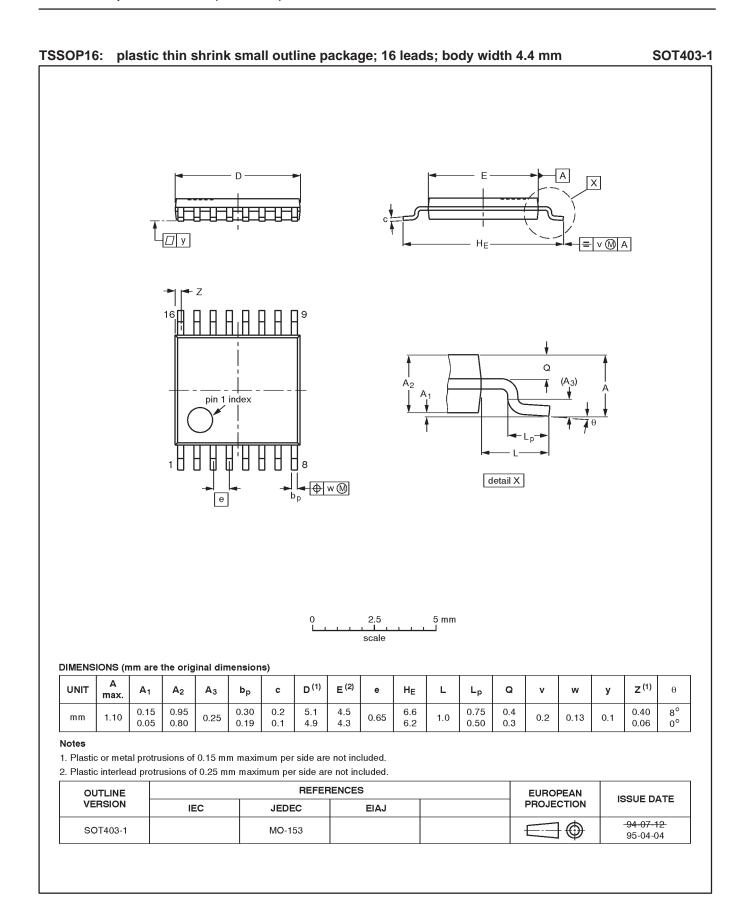
74LV595



74LV595



74LV595



74LV595

NOTES

### 74LV595

	DEFINITIONS						
Data Sheet Identification	Product Status	Definition					
<b>Objective Specification</b>	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.					
Preliminary Specification	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.					
Product Specification	Full Production	This data sheet contains Final Specifications. Philips Semiconductors reserves the right to make changes at any time without notice, in order to improve design and supply the best possible product.					

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